

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

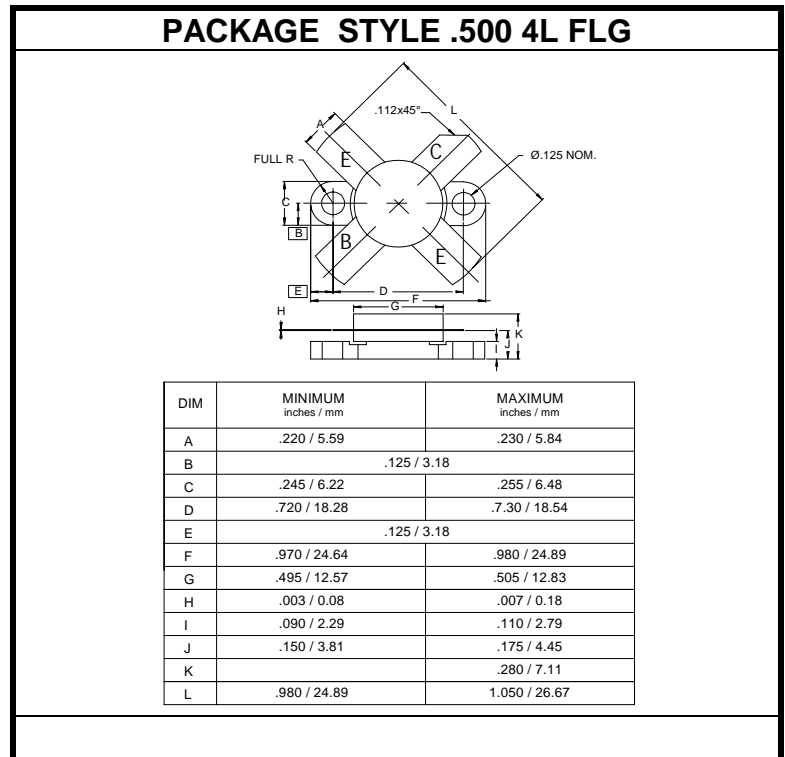
The **ASI BLW97** is Designed for High voltage applications up to 30 MHz

FEATURES:

- $P_G = 11.5$ dB min. at 175 W/30 MHz
- $IMD_3 = -30$ dBc max. at 175 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	15 A
V_{CESM}	65 V
V_{CEO}	33 V
V_{EBO}	4.0 V
P_{DISS}	230 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.76 °C/W



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50$ mA	65			V
BV_{CEO}	$I_C = 100$ mA	33			V
BV_{EBO}	$I_E = 20$ mA	4.0			V
I_{CES}	$V_{CE} = 33$ V			20	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 10$ A	15		50	---
$V_{CE(SAT)}$	$I_C = 25$ A $I_B = 5.0$ A			2.4	V
C_C	$V_{CB} = 28$ V $f = 1.0$ MHz		380		pF
G_P	$V_{CE} = 28$ V $I_{CQ} = 100$ mA $P_{OUT} = 175$ W (PEP)	11.5			dB
IMD_3				-30	dBc
η_C		40			%

IMPEDANCE DATA

FREQ.	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$	$P_{IN}(W)$	$V_{CE}(V)$
470 MHz	$1.5 - j2.7$	$5.7 + j1.5$	2.0	12.5